

AMENDMENT TO THE ABSTRACTAbstract of Disclosure ABSTRACT OF DISCLOSURE

~~The present invention relates to a~~ A photopolymerizable resin composition for sandblast resist, ~~which comprises,~~ includes as a photopolymerizable oligomer, a polyalkylene glycol mono(~~meta~~ meth)acrylate compound having a terminal alkyl group, a compound selected from polyalkylene glycol di(~~meta~~ meth)acrylate compounds, and further a compound selected from urethane compounds having a terminal (~~meta~~ meth)acrylate group as derived from a polyether or polyester compound having a terminal hydroxyl group, a diisocyanate compound and a (~~meta~~ meth)acrylate compound having a hydroxyl group. The resist containing the photopolymerizable resin composition exhibits much improved reactivity relative to the resist using a urethane compound having a terminal (~~meta~~ meth)acrylate group alone or in combination with an unsaturated (~~meta~~ meth)acrylate compound, which has been conventionally used for dry films. Particularly, it guarantees remarkable improvement in the damage on the surface of the photopolymerizable resin composition after development for the cured regions, which damage is much serious for the resin composition using a cellulose compound having a carboxyl group as an aqueous alkali-soluble polymer. ~~Consequently, a sandblast resist for realization of high resolution or fabrication of high resolution PDPs can be provided according to the present invention.~~